

2N3019, 2N3019S

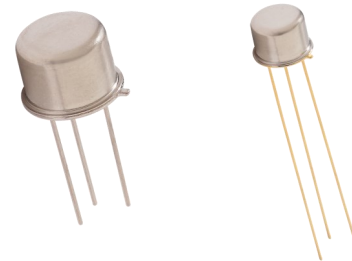


NPN Low Power Silicon Transistor

Rev. V2

Features

- JAN, JANTX, JANTXV, JANS and JANSR Qualified to MIL-PRF-19500/391
- Lightweight & Low Power
- Ideal for Space, Military, & Other High Reliability Applications
- Available in TO-5 and TO-39 packages



Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_C = 30 \text{ mA}$	$V_{(BR)CEO}$	V dc	80	—
Collector - Base Cutoff Current	$V_{CB} = 140 \text{ V}$	I_{CBO1}	μA dc	—	10
Emitter - Base Cutoff Current	$V_{EB} = 7 \text{ V}$	I_{EBO1}	μA dc	—	10
Collector - Emitter Cutoff Current	$V_{CE} = 90 \text{ V}$	I_{CES1}	nA dc	—	10
Emitter - Base Cutoff Current	$V_{EB} = 5 \text{ Vdc}$	I_{EBO2}	nA dc	—	10
Forward Current Transfer Ratio	$V_{CE} = 10 \text{ V dc}; I_C = 150 \text{ mA dc}$	h_{FE1}		100	300
	$V_{CE} = 10 \text{ V dc}; I_C = 0.1 \text{ mA dc}$	h_{FE2}		50	300
	$V_{CE} = 10 \text{ V dc}; I_C = 10 \text{ mA dc}$	h_{FE3}		90	
	$V_{CE} = 10 \text{ V dc}; I_C = 500 \text{ mA dc}$	h_{FE4}	-	50	300
	$V_{CE} = 10 \text{ V dc}; I_C = 1 \text{ A dc}$	h_{FE5}		15	
Collector - Emitter Saturation Voltage	$I_C = 150 \text{ mA}; I_B = 15 \text{ mA}$	$V_{CE(SAT)1}$	V dc	—	0.2
	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	$V_{CE(SAT)2}$			0.5
Base - Emitter Saturation Voltage	$I_C = 150 \text{ mA}; I_B = 15 \text{ mA}$	$V_{BE(SAT)}$	V dc	—	1.1
Collector - Emitter Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CE} = 90 \text{ V}$	I_{CES2}	μA dc	—	5
Forward Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $V_{CE} = 10 \text{ V dc}; I_C = 150 \text{ mA dc}$	h_{FE6}		40	

Safe Operating Area

DC Tests:	$T_C = +25^\circ\text{C}; 1\text{Cycle}, t = 10 \text{ ms}$
Test 1:	$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA dc}$
Test 2:	$V_{CE} = 40 \text{ V}, I_C = 130 \text{ mA dc}$
Test 3:	$V_{CE} = 80 \text{ V}, I_C = 60 \text{ mA dc}$

1

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2N3019, 2N3019S



NPN Low Power Silicon Transistor

Rev. V2

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Dynamic Characteristics					
Small-Signal Short-Circuit Forward -Current Transfer Ratio	$V_{CE} = 5 \text{ V dc}; I_C = 1 \text{ mA dc}; f = 1 \text{ kHz}$	h_{FE}		80	400
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	$V_{CE} = 10 \text{ V dc}; I_C = 50 \text{ mA dc}; f = 20 \text{ MHz}$	$ h_{FE} $		5	20
Input Capacitance (Output Open Circuited)	$V_{EB} = 0.5 \text{ V dc}; I_C = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{ibo}	pF	—	60
Open Circuit Output Capacitance	$V_{CB} = 10 \text{ V dc}; I_E = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{obo}	pF	—	12
Noise Figure	$V_{CE} = 10 \text{ V dc}; I_C = 100 \mu\text{A dc}; R_g = 1 \text{ k}\Omega;$ power bandwidth = 200 Hz $f = 1 \text{ kHz}$	NF	dB	—	4
Pulse Response	See Figure 21 of MIL-PRF-19500/391	$t_{on}+t_{off}$	ns		30

Absolute Maximum Ratings ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage	V_{CEO}	80 V dc
Collector - Base Voltage	V_{CBO}	140 V dc
Emitter - Base Voltage	V_{EBO}	7 V dc
Collector Current	I_C	1 A dc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$	$P_T^{(1)(2)}$	0.8 W 5.0 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to $+200^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case ⁽²⁾⁽³⁾	$R_{\theta JC}$	30°C/W
Thermal Resistance, Junction to Ambient ⁽²⁾⁽³⁾	$R_{\theta JA}$	195°C/W

(1) For derating, see figures 8, 9, 10, 11, 12 and 13 of MIL-PRF-19500/391

(2) See paragraph 3.3 of MIL-PRF-19500/391

(3) For thermal curves, see figures 14, 15, 16, 17, 18, 19 and 20 of MIL-PRF-19500/391

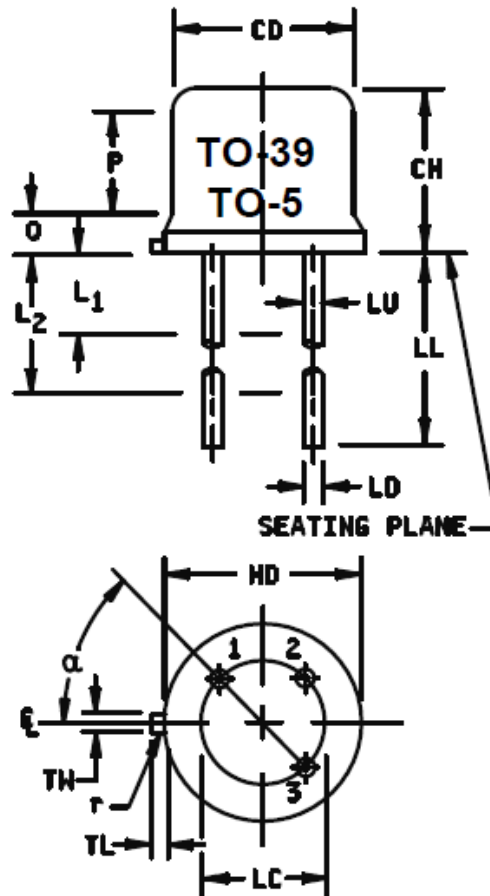
2N3019, 2N3019S

NPN Low Power Silicon Transistor

Rev. V2

Outline Drawing (TO-5, TO-39)

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		6
LD	.016	.021	0.41	0.53	7, 8
LL	1.50	1.750	38.10	40.45	7, 8, 12
LU	.016	.019	0.41	0.48	7, 8
L ₁		.050		1.27	7, 8
L ₂	.250		6.35		7, 8
Q		.050		1.27	5
TL	.029	.045	0.74	1.14	4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45° TP		45° TP		6
P	.100		2.54		

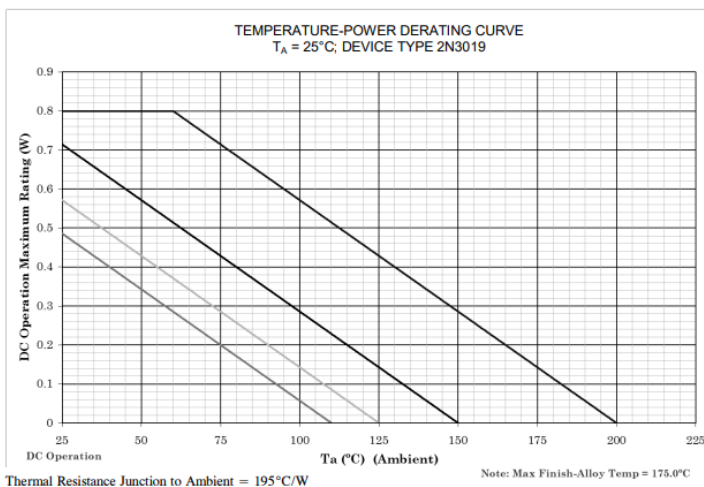


NOTES:

1. Dimension are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
7. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
12. For "S" suffix devices, dimension LL is 0.500 (12.70 mm) minimum, 0.750 (19.05 mm) maximum.
13. Lead 1 = emitter, lead 2 = base, lead 3 = collector.

* FIGURE 1. Physical dimensions for device types 2N3019 (TO-5) and 2N3019S (TO-39).

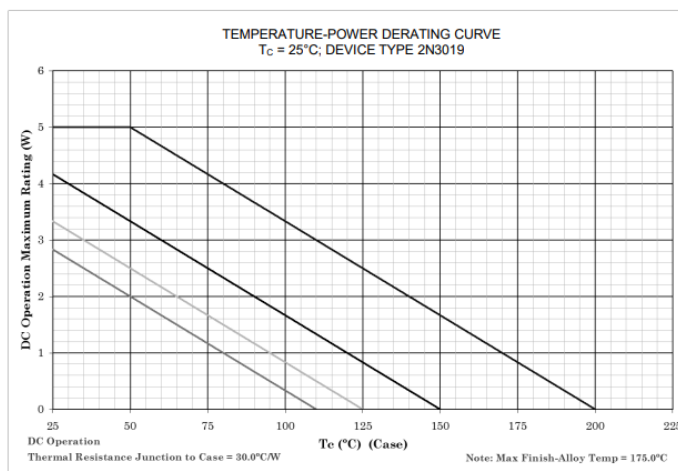
Temperature-Power Derating Curve



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq +125^\circ\text{C}$, and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

FIGURE 8. Derating for 2N3019 ($R_{\theta JA}$) PCB (TO-5 and TO-39).



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FIGURE 9. Derating for 2N3019 ($R_{\theta JC}$), base case mounted (TO-5 and TO-39).

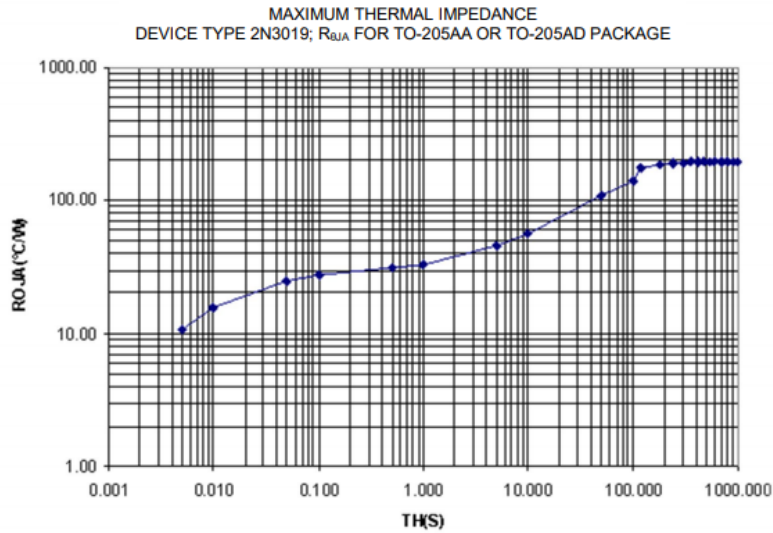
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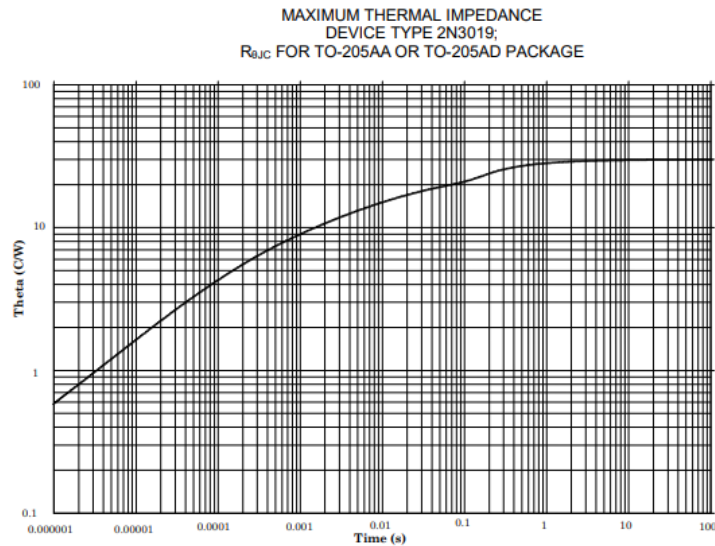
Rev. V2

Thermal Impedance Curve



$R_{\theta JA} = 195^{\circ}\text{C/W}$

FIGURE 14. Thermal impedance graph ($R_{\theta JA}$) for a 2N3019 in a TO-205AA or TO-205AD package.



$R_{\theta JC} = 30^{\circ}\text{C/W}$

FIGURE 15. Thermal impedance graph ($R_{\theta JC}$) for a 2N3019 in a TO-205AA or TO-205AD package.

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NPN Low Power Silicon Transistor

Rev. V2

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